

Dual N-Ch 40V Fast Switching MOSFETs

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

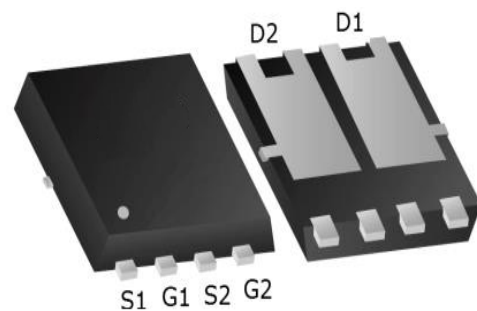


BVDSS	RDS(on)	ID
40V	17mΩ	20A

Description

The UD4886D is the high cell density trench N-ch MOSFETs, which provide excellent RDS(on) and gate charge for most of the synchronous buck converter applications. The UD4886D meet the RoHS and Green Product

PDFN3333-8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	40	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _A =25°C	Continuous Drain Current ¹	20	A
I _D @T _A =70°C	Continuous Drain Current ¹	13	A
I _{DM}	Pulsed Drain Current ²	43	A
EAS	Single Pulse Avalanche Energy ³	13	mJ
I _{AS}	Avalanche Current	20	A
P _D @T _A =25°C	Total Power Dissipation ⁴	3.0	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ¹ (t≤10s)	---	62.5	°C/W
	Thermal Resistance Junction-ambient ¹	---	65	°C/W

N-Channel Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =40V, V _{GS} =0V	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =10V, I _D =8A	-	17	22	mΩ
		V _{GS} =4.5V, I _D =5A	-	25	35	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =20V, V _{GS} =0V, f=1.0MHz	-	633	-	pF
C _{oss}	Output Capacitance		-	67	-	pF
C _{rss}	Reverse Transfer Capacitance		-	58	-	pF
Q _g	Total Gate Charge	V _{DS} =20V, I _D =8A, V _{GS} =10V	-	12	-	nC
Q _{gs}	Gate-Source Charge		-	3.2	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	3.1	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = 20V, R _L =2.5Ω V _{GS} =10V,R _{REN} =3Ω	-	4	-	ns
t _r	Turn-on Rise Time		-	3	-	ns
t _{d(off)}	Turn-off Delay Time		-	15	-	ns
t _f	Turn-off Fall Time		-	2	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	8	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	32	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = 8A	-	-	1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : $T_J=25^\circ\text{C}, V_{DD}=20V, V_G=10V, L=0.5mH, R_g=25\Omega, I_{AS}=7.2A$

$T_J=25^\circ\text{C}, V_{DD}=-20V, V_G=-10V, L=0.5mH, R_g=25\Omega, I_{AS}=-8.4A$

3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

Typical Performance Characteristics-N

Figure 1: Output Characteristics

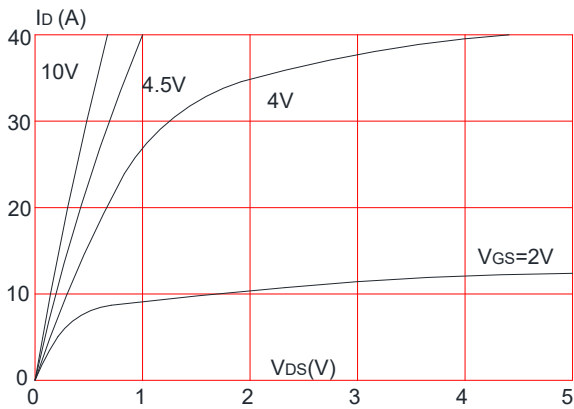


Figure 2: Typical Transfer Characteristics

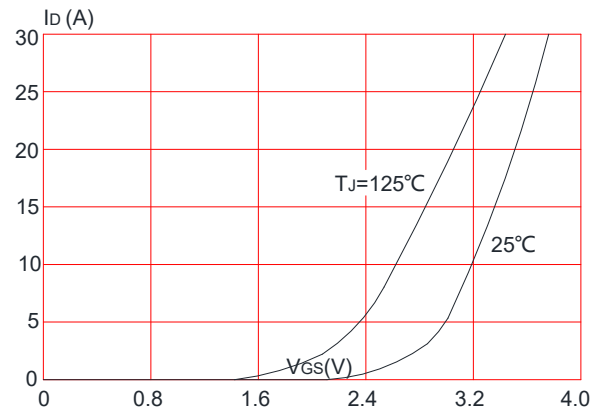


Figure 3: On-resistance vs. Drain Current

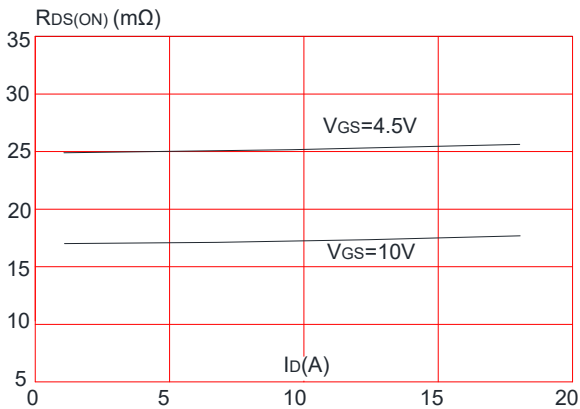


Figure 4: Body Diode Characteristics

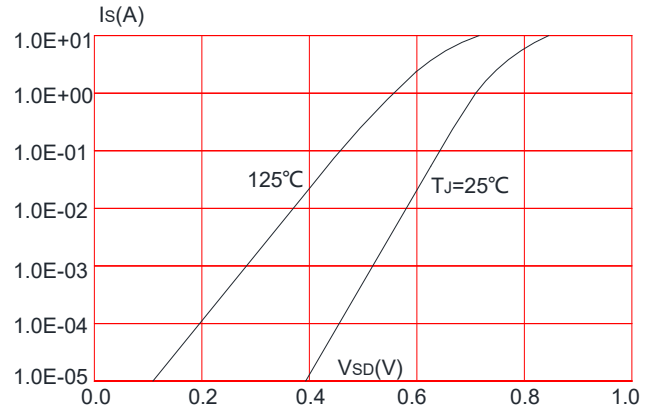


Figure 5: Gate Charge Characteristics

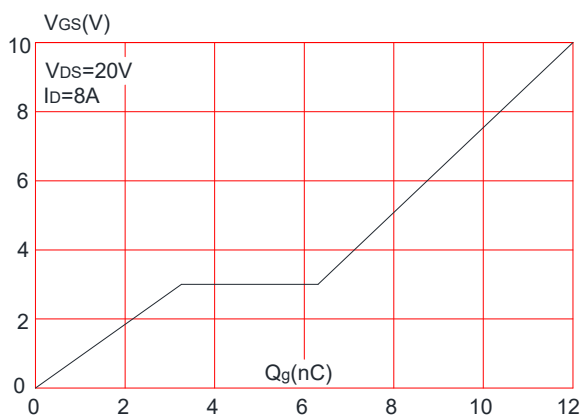
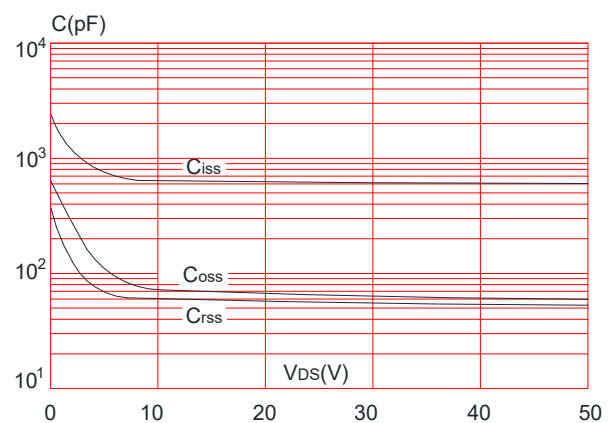


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

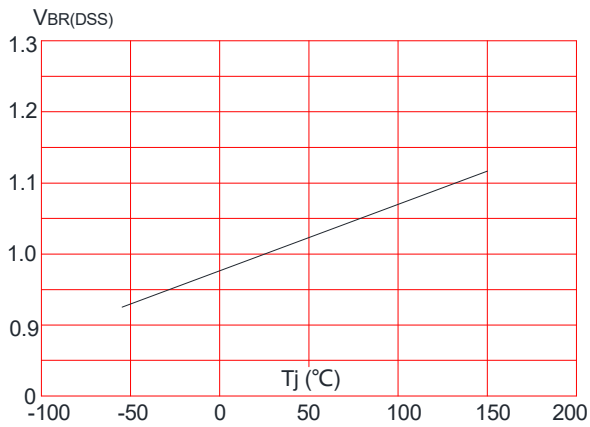


Figure 8: Normalized on Resistance vs. Junction Temperature

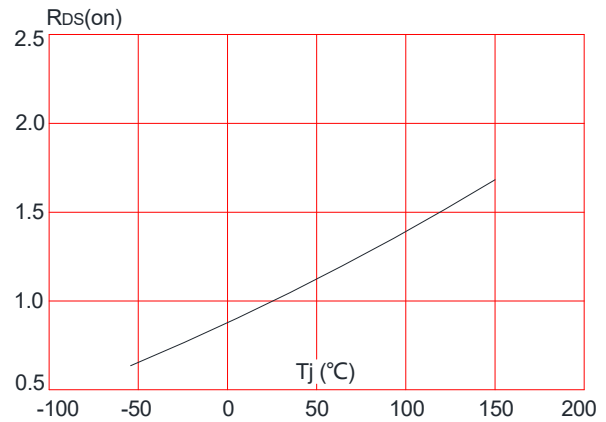


Figure 9: Maximum Safe Operating Area

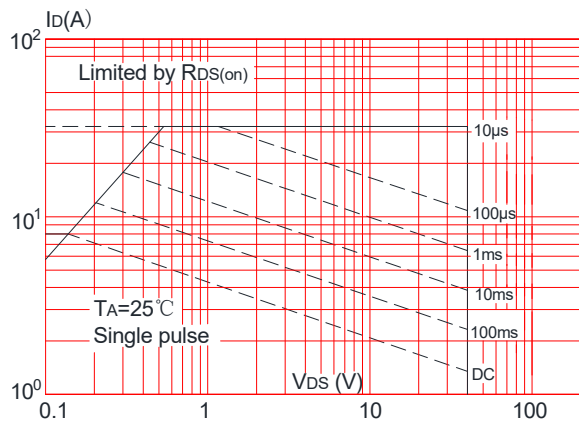


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

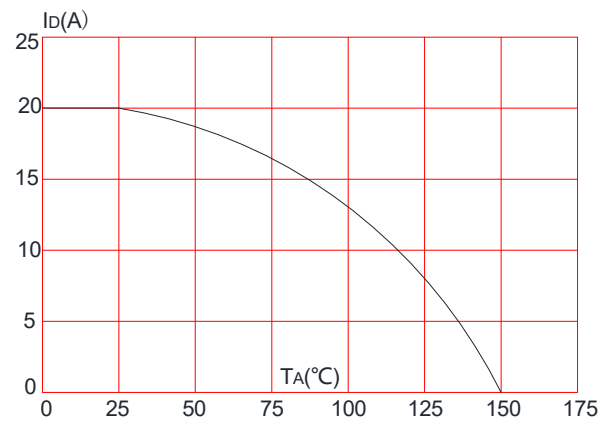
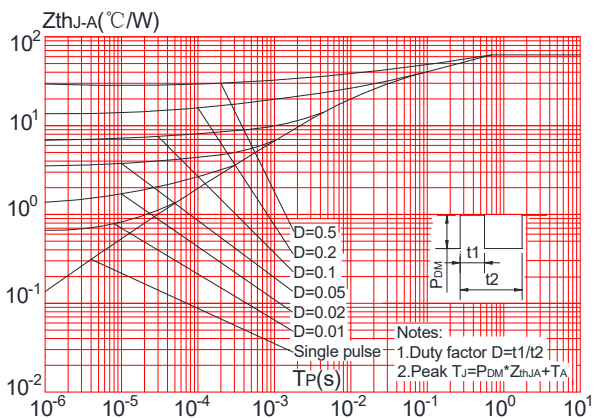
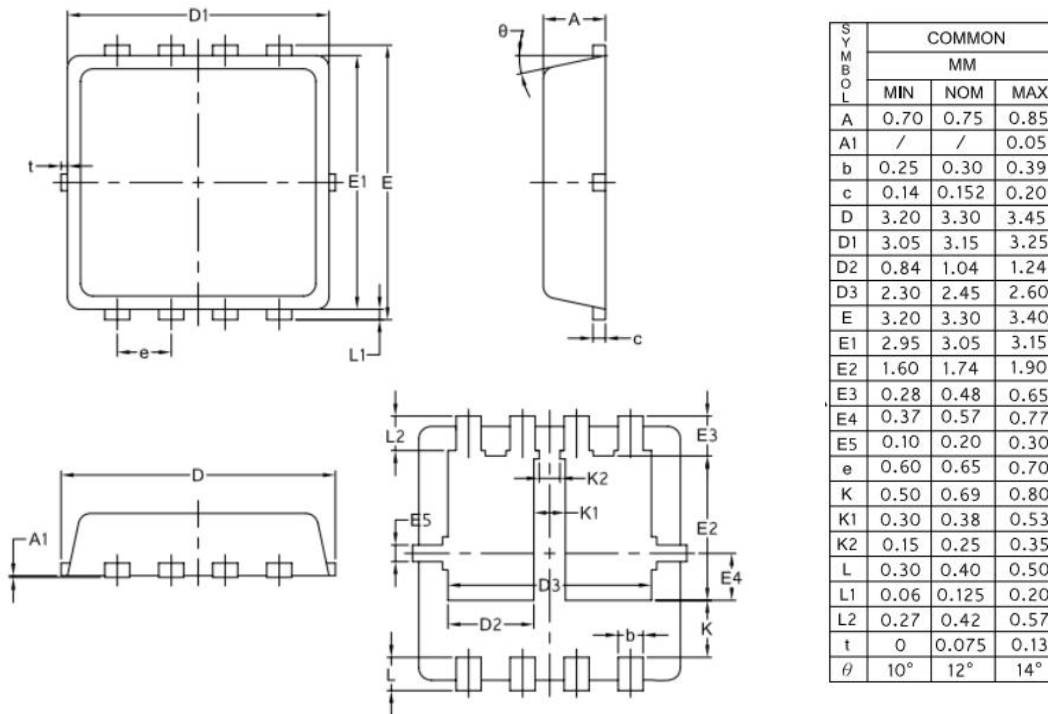


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Package Mechanical Data-PDFN3333-8L-D-Type A



Package Mechanical Data-PDFN3333-8L-D-Type B

